

REMARKS

Prior to further examination on the merits and supplemental to the Preliminary Amendment filed November 19, 2002, applicants request entry of this Supplemental Preliminary Amendment. Claims 1-11, 15-21, 23, and 25-31 were pending in the application. Claims 1, 4, 11, 15, and 23 have been amended, no claims have been canceled and new claims 32 and 33 have been added. Therefore, claims 1-11, 15-21, 23, and 25-33 are pending in the application and are submitted for consideration by the examiner.

Claims 1, 4, 11, 15, and 23 have been amended to better define the invention. New claims 32 and 33 have been added to recite additional features of the invention. No new matter has been added. Applicants believe that the pending claims are distinguishable over the applied prior art and a notification of the same is respectfully requested.

If there are any questions regarding the application or if an examiner's amendment or an interview would facilitate the allowance of one or more of the claims, the examiner is courteously invited to contact the undersigned attorney at the local number below.

Respectfully submitted,

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By

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Should additional fees be necessary in connection with the filing of this paper, or if a petition for extension of time is required for timely acceptance of same, the Commissioner is hereby authorized to charge deposit account No. 19-0741 for any such fees; and applicants hereby petition for any needed extension of time.

ATTACHMENT A

Marked up version of claim amendments made in the Supplemental Preliminary Amendment filed December 3, 2002:

1. (Four Times Amended) A semiconductor device comprising:
a pair of main electrodes used as source and drain electrodes;
a channel forming region provided between the pair of main electrodes;
an insulating gate film [adjacent to the a pair of main electrodes] formed on the channel forming region; and
a gate electrode [comprising of] formed on the insulating gate film, and provided with
a first region including at least a first group IV element and a second group IV element and
formed in contact with the insulating gate film, and a second region including the first group
IV element and formed on the first region, the first [region] and second [region] regions
having an identical conductivity type.

4. (Four Times Amended) A semiconductor device comprising:
an insulated gate field effect transistor having a pair of main electrodes used as source
and drain electrodes, a channel forming region provided between the pair of main electrodes,
an insulating gate film [adjacent to the a pair of main electrodes] formed on the channel
forming region, and a gate electrode [comprising] formed on the insulating gate film, and
provided with a first region including at least a first group IV element and a second group IV
element and formed in contact with the insulating gate film, and a second region including the
first group IV element and formed on the first region, the first [region] and second [region]
regions having an identical conductivity type; and
a silicide electrode formed in contact with the second region of the gate electrode, and
being substantially free from the second group IV element.

11. (Four Times Amended) A semiconductor device comprising:
an insulated gate field effect transistor having a pair of main electrodes used as source
and drain electrodes, a channel forming region provided between the pair of main electrodes,

an insulating gate film [adjacent to the a pair of main electrodes] formed on the channel forming region, and a gate electrode [comprising] formed on the insulating gate film, and provided with a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including a multiple element compound including at least the first and second group IV elements and metal, and formed on the first region, the first [region] and second [region] regions having an identical conductivity type; and

a silicide electrode formed in contact with the second region of the gate electrode, including the first group IV element and metal, and being substantially free from the second group IV element.

15. (Three Times Amended) A semiconductor device comprising:

a semiconductor region of a first conductivity type;

an epitaxial growth layer formed on the semiconductor region and having a first region of the first conductivity type including at least a first group IV element and a second group IV element and formed in contact with the semiconductor region, and a second region of the first conductivity type including the first group IV element and formed in contact with the first region; and

a silicide electrode formed on the second region of the epitaxial growth layer.

23. (Four Times Amended) A semiconductor device comprising:

an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film [adjacent to the a pair of main electrodes] formed on the channel forming region, and a gate electrode [comprising] formed on the insulating gate film, and provided with a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region, the first [region] and second [region] regions having an identical conductivity type;

a respective elevated electrode formed on the main electrodes, and having a third region including a third group IV element and a fourth group IV element and a fourth region formed on the third region and including the third group IV element;

a first silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element; and

a second silicide electrode formed in contact with the fourth region of the elevated electrode, and being substantially free from the fourth group IV element.